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SEMICONDUCTOR DEVICE AND METHOD OF PROVIDING REGIONS OF LOW  
SUBSTRATE CAPACITANCE

Abstract of the Disclosure

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A semiconductor device (2) includes a semiconductor substrate (12) having a surface (13) formed with a first recessed region (20). A first dielectric material (60) is deposited in the first recessed region and formed with a second recessed region (76), and a second dielectric material (100) is grown over the first dielectric material to seal the second recessed region.

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